

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	30	(SRAM or (static adj6 random adj5 access adj5 memory)) same (true adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:36
L2	6	((SRAM or (static adj6 random adj5 access adj5 memory)) same (true adj3 bit\$1line)) same (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:37
L3	4	((("true bit line" or (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)) and pre\$1charg\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:38
L4	88	(bit\$1line and (complement adj3 bit\$1lin\$2) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:39
L5	34	((((bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$4) and (FET or "field effect transistor" or transistor)) and SRAM) and "365"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:39
L6	9	((((bit\$1line and (complement adj4 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM) and 365/201.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:40
L7	5	((((bit\$1line and (complement adj4 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM) and 365/154.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:41
S1	48048	SRAM or (static adj5 random adj5 access adj5 memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:39
S2	28	(SRAM or (static adj5 random adj5 access adj5 memory)) same (true adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:36

S3	6	((SRAM or (static adj5 random adj5 access adj5 memory)) same (true adj3 bit\$1line)) same (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:37
S4	69	(SRAM or (static adj5 random adj5 access adj5 memory)) and (true adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:41
S5	6	((SRAM or (static adj5 random adj5 access adj5 memory)) and (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:41
S6	6	("true bit line" or (true adj3 bit\$1line)) same (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:43
S7	16	("true bit line" or (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:38
S8	4	((("true bit line" or (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)) and pre\$1charg\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:38
S9	11	("bit line" or (true adj3 bit\$1line)) same (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:43
S10	27	("bit line" or (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:44
S11	4	((("bit line" or (true adj3 bit\$1line)) and (continuous adj3 bit\$1line)) and pre\$1charg\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:44
S12	75	bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:45

S13	68	(bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:38
S14	36	((bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:46
S15	32	((bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM) and "365"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:39
S16	5	((bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM) and 365/154.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:40
S17	9	((bit\$1line and (complement adj3 bit\$1lin\$1) and pre\$1charg\$3) and (FET or "field effect transistor" or transistor)) and SRAM) and 365/201.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/16 17:39
S18	0	adam-chad-a.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:47
S19	0	adams-chad-a.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:47
S20	0	aipperspach-anthony.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:47
S21	42	aipperspach-anthony-\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:47
S22	0	christensen-todd.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:48

S23	41	christensen-todd-\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:48
S24	0	freiburger-peter.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 00:48
S25	12	freiburger-peter-\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/12 02:56